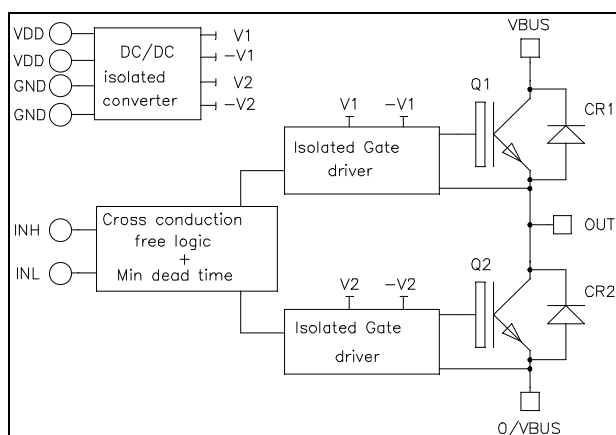


## Phase leg Intelligent Power Module

$V_{CES} = 600V$   
 $I_C = 400A @ T_c = 80^\circ C$

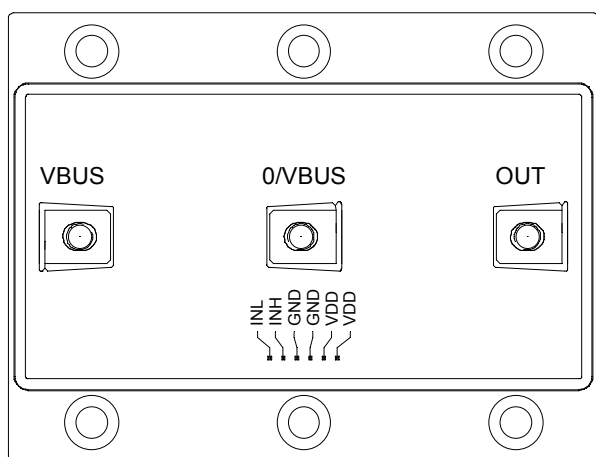


### Application

- Motor control
- Uninterruptible Power Supplies
- Switched Mode Power Supplies
- Amplifier

### Features

- **Non Punch Through (NPT) FAST IGBT**
  - Low voltage drop
  - Low tail current
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA & SCSOA rated
- **Integrated Fail Safe IGBT Protection (Driver)**
  - Top Bottom input signals Interlock
  - Isolated DC/DC Converter



- Low stray inductance
- M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very high noise immunity (common mode rejection > 25kV/μs)
- Galvanic Isolation: 3750V for the optocoupler  
2500V for the transformer
- 5V logic level with Schmitt-trigger Input
- Single  $V_{DD}=5V$  supply required
- Secondary auxiliary power supplies internally generated (15V, -6V)
- Optocoupler qualified to AEC-Q100 test guidelines
- RoHS compliant



**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.  
See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

**All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified**

## 1. Inverter Power Module

### Absolute maximum ratings

| Symbol    | Parameter                             | Max ratings                            | Unit |
|-----------|---------------------------------------|----------------------------------------|------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage | 600                                    | V    |
| $I_C$     | Continuous Collector Current          | $T_C = 25^\circ\text{C}$<br>600        | A    |
|           |                                       | $T_C = 80^\circ\text{C}$<br>400        |      |
| $I_{CM}$  | Pulsed Collector Current              | $T_C = 25^\circ\text{C}$<br>800        |      |
| $P_D$     | Maximum Power Dissipation             | $T_C = 25^\circ\text{C}$<br>1250       | W    |
| RBSOA     | Reverse Bias Safe Operating Area      | $T_j = 150^\circ\text{C}$<br>800A@550V |      |

### Electrical Characteristics

| Symbol        | Characteristic                       | Test Conditions                                       | Min | Typ | Max | Unit |
|---------------|--------------------------------------|-------------------------------------------------------|-----|-----|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0\text{V}$<br>$V_{CE} = 600\text{V}$        |     |     | 0.3 | mA   |
|               |                                      | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ |     |     | 1   |      |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{DD} = V_{IN} = 5\text{V}$<br>$I_C = 400\text{A}$  |     | 1.5 | 1.9 | V    |
|               |                                      | $T_j = 25^\circ\text{C}$<br>$T_j = 150^\circ\text{C}$ |     | 1.7 |     |      |

### Dynamic Characteristics

| Symbol     | Characteristic                      | Test Conditions                                                                                                                | Min | Typ  | Max  | Unit               |
|------------|-------------------------------------|--------------------------------------------------------------------------------------------------------------------------------|-----|------|------|--------------------|
| $C_{ies}$  | Input Capacitance                   | $V_{GE} = 0\text{V}$<br>$V_{CE} = 25\text{V}$<br>$f = 1\text{MHz}$                                                             |     | 24   |      | nF                 |
| $C_{oes}$  | Output Capacitance                  |                                                                                                                                |     | 1.6  |      |                    |
| $C_{res}$  | Reverse Transfer Capacitance        |                                                                                                                                |     | 0.8  |      |                    |
| $T_r$      | Rise Time                           | Inductive Switching ( $25^\circ\text{C}$ )<br>$V_{DD} = V_{IN} = 5\text{V}$<br>$V_{Bus} = 300\text{V}$ ; $I_C = 400\text{A}$   |     | 45   |      | ns                 |
| $T_f$      | Fall Time                           |                                                                                                                                |     | 55   |      |                    |
| $T_r$      | Rise Time                           | Inductive Switching ( $125^\circ\text{C}$ )<br>$V_{DD} = V_{IN} = 5\text{V}$<br>$V_{Bus} = 300\text{V}$<br>$I_C = 400\text{A}$ |     | 25   |      | ns                 |
| $T_f$      | Fall Time                           |                                                                                                                                |     | 70   |      |                    |
| $E_{on}$   | Turn-on Switching Energy            | $V_{DD} = V_{IN} = 5\text{V}$ ; $V_{Bus} = 360\text{V}$<br>$t_p \leq 6\mu\text{s}$ ; $T_j = 150^\circ\text{C}$                 |     | 3.5  |      | mJ                 |
| $E_{off}$  | Turn-off Switching Energy           |                                                                                                                                |     | 14   |      |                    |
| $I_{sc}$   | Short Circuit data                  | $V_{DD} = V_{IN} = 5\text{V}$ ; $V_{Bus} = 360\text{V}$<br>$t_p \leq 6\mu\text{s}$ ; $T_j = 150^\circ\text{C}$                 |     | 2000 |      | A                  |
| $R_{thJC}$ | Junction to Case thermal resistance |                                                                                                                                |     |      | 0.12 | $^\circ\text{C/W}$ |

**Reverse diode ratings and characteristics**

| Symbol            | Characteristic                          | Test Conditions                                                    |                                                 | Min | Typ        | Max        | Unit |
|-------------------|-----------------------------------------|--------------------------------------------------------------------|-------------------------------------------------|-----|------------|------------|------|
| V <sub>RRM</sub>  | Maximum Peak Repetitive Reverse Voltage |                                                                    |                                                 | 600 |            |            | V    |
| I <sub>RM</sub>   | Maximum Reverse Leakage Current         | V <sub>R</sub> =600V                                               | T <sub>i</sub> = 25°C<br>T <sub>i</sub> = 150°C |     |            | 350<br>500 | μA   |
| I <sub>F</sub>    | DC Forward Current                      |                                                                    | T <sub>c</sub> = 80°C                           |     | 400        |            | A    |
| V <sub>F</sub>    | Diode Forward Voltage                   | I <sub>F</sub> = 400A                                              | T <sub>i</sub> = 25°C<br>T <sub>i</sub> = 150°C |     | 1.6<br>1.5 | 2          | V    |
| t <sub>rr</sub>   | Reverse Recovery Time                   | I <sub>F</sub> = 400A<br>V <sub>R</sub> = 300V<br>di/dt = 4800A/μs | T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 150°C |     | 125<br>220 |            | ns   |
| Q <sub>rr</sub>   | Reverse Recovery Charge                 |                                                                    | T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 150°C |     | 19<br>40   |            | μC   |
| E <sub>rr</sub>   | Reverse Recovery Energy                 |                                                                    | T <sub>j</sub> = 25°C<br>T <sub>j</sub> = 150°C |     | 4.4<br>9.6 |            | mJ   |
| R <sub>thJC</sub> | Junction to Case thermal resistance     |                                                                    |                                                 |     |            | 0.20       | °C/W |

**2. Driver**
**Absolute maximum ratings**

| Symbol              | Parameter                   | Max ratings                                                                          | Unit |   |
|---------------------|-----------------------------|--------------------------------------------------------------------------------------|------|---|
| V <sub>DD</sub>     | Supply Voltage              | 5.5                                                                                  | V    |   |
| V <sub>INi</sub>    | Input signal voltage i=L, H | 5.5                                                                                  |      |   |
| I <sub>VDDmax</sub> | Maximum Supply current      | V <sub>INi</sub> = 0V, i = L & H                                                     | 0.35 | A |
|                     |                             | V <sub>DD</sub> =5V, V <sub>INH</sub> = /V <sub>INL</sub> ; F <sub>out</sub> = 45kHz | 2    |   |
| f <sub>max</sub>    | Maximum Switching Frequency | 45                                                                                   | kHz  |   |

**Driver Electrical Characteristics**

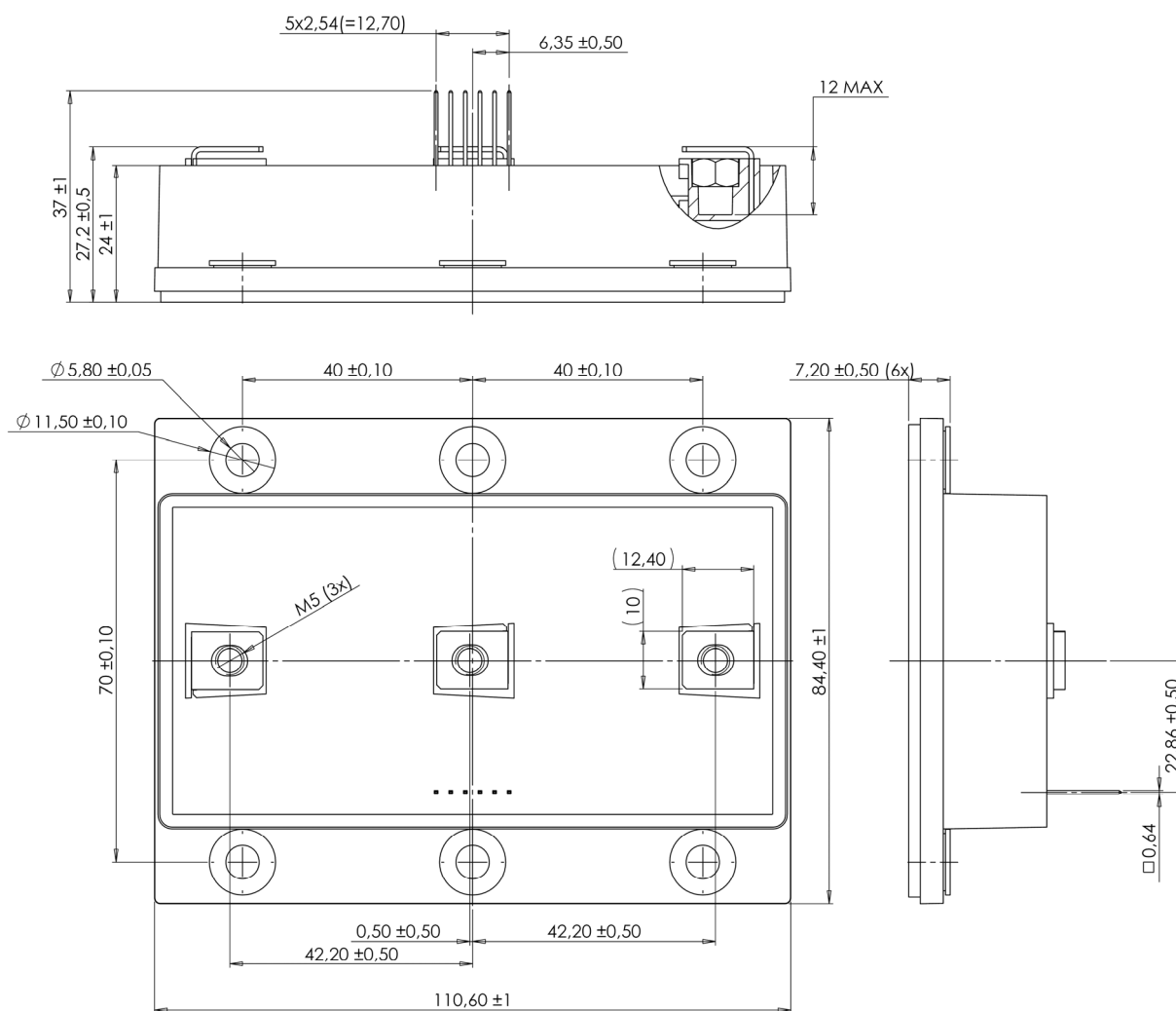
| Symbol                | Characteristic                                      | Test Conditions                          | Min  | Typ               | Max | Unit             |
|-----------------------|-----------------------------------------------------|------------------------------------------|------|-------------------|-----|------------------|
| V <sub>DD</sub>       | Operating Supply Voltage                            |                                          | 4.5  | 5                 | 5.5 | V                |
| V <sub>INi(max)</sub> | Maximum Input Voltage                               | i = L, H                                 | -0.5 | 5                 | 5.5 | V                |
| V <sub>INi(th+)</sub> | Positive Going Threshold Voltage                    |                                          |      | 3.2               |     |                  |
| V <sub>INi(th-)</sub> | Negative Going Threshold Voltage                    |                                          |      | 1                 |     |                  |
| R <sub>INi</sub>      | Input Resistance *                                  |                                          |      | 1                 |     | kΩ               |
| T <sub>d(on)</sub>    | Turn On delay time                                  | Driver + IGBT                            |      | 1100 <sup>●</sup> |     | ns               |
| D <sub>T</sub>        | Built in dead time                                  |                                          |      | 600               |     |                  |
| T <sub>d(off)</sub>   | Turn Off delay time                                 | Driver + IGBT                            |      | 750               |     |                  |
| PWD                   | Pulse Width Distortion                              |                                          |      |                   | 300 | ns               |
| PDD                   | Propagation Delay Difference between any two driver | T <sub>d(on)</sub> - T <sub>d(off)</sub> | -350 |                   | 350 |                  |
| V <sub>ISOL</sub>     | Primary to Secondary Isolation                      |                                          | 2500 |                   |     | V <sub>RMS</sub> |

\* Low impedance guarantees good noise immunity.

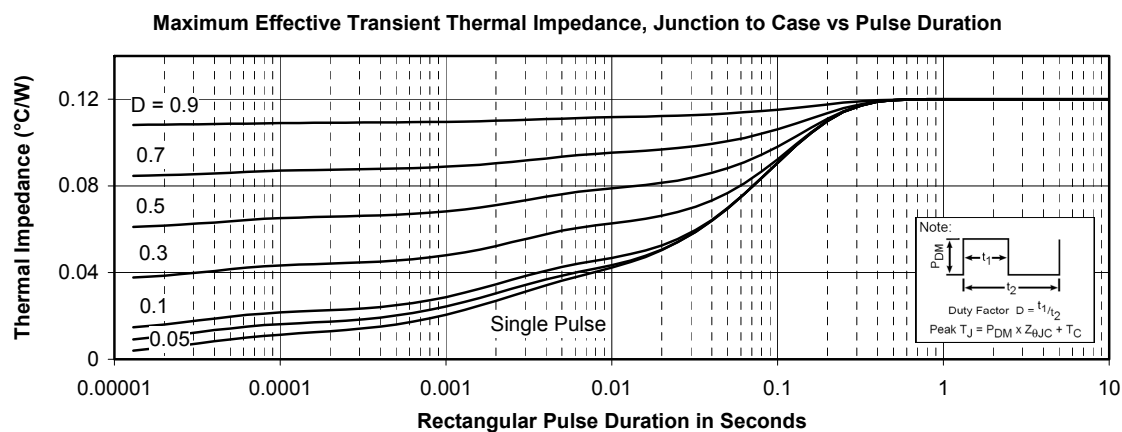
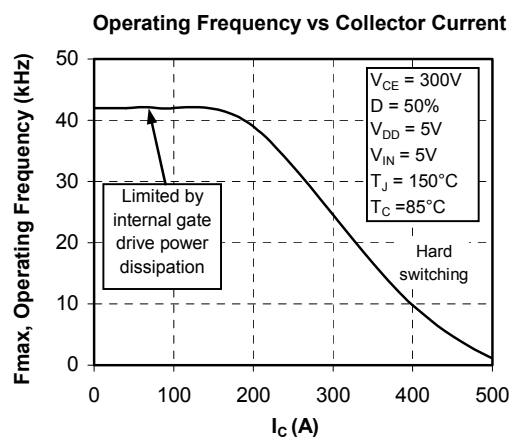
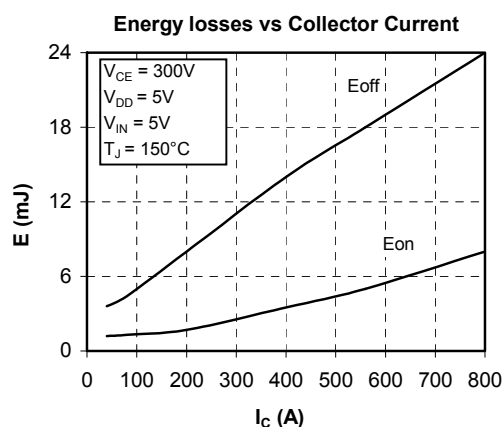
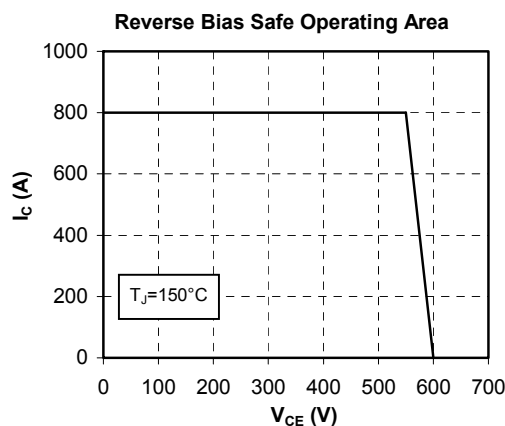
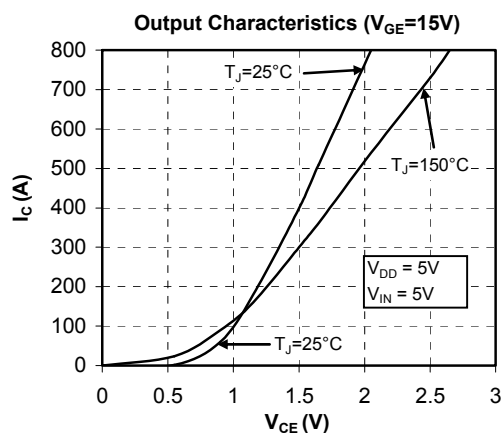
## 3. Package characteristics

| Symbol            | Characteristic                                                | Min           | Typ | Max | Unit |
|-------------------|---------------------------------------------------------------|---------------|-----|-----|------|
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | 4000          |     |     | V    |
| T <sub>J</sub>    | Operating junction temperature range                          | -40           |     | 150 | °C   |
| T <sub>OP</sub>   | Operating Ambient Temperature                                 | -40           |     | 85  |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     | -40           |     | 100 |      |
| T <sub>C</sub>    | Operating Case Temperature                                    | -40           |     | 100 |      |
| Torque            | Mounting torque                                               | To heatsink   | M5  | 2   | N.m  |
|                   |                                                               | For terminals | M5  | 2   |      |
| Wt                | Package Weight                                                |               | 550 |     | g    |

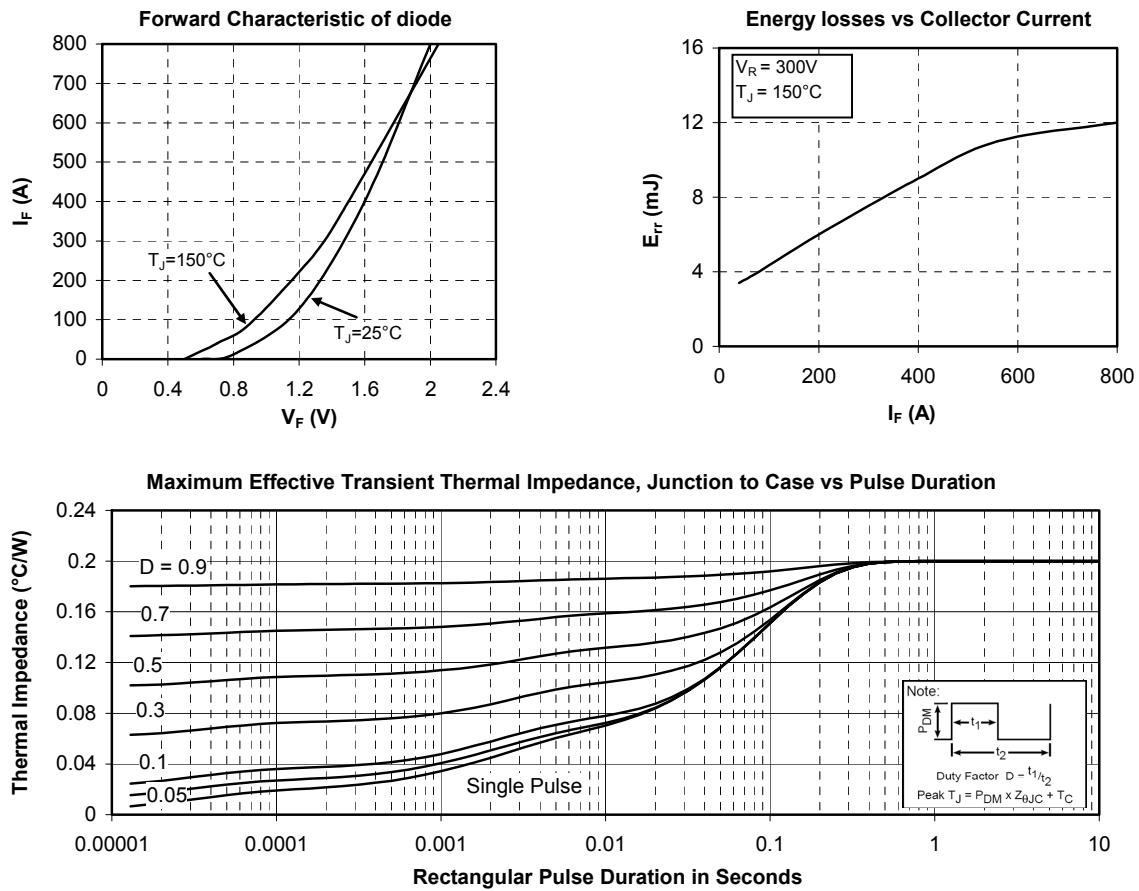
## 4. LP8 Package outline (dimensions in mm)



## Typical IGBT Performance Curve



## Typical diode Performance Curve



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